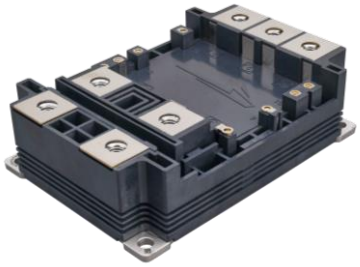
# CAB600M33LM3

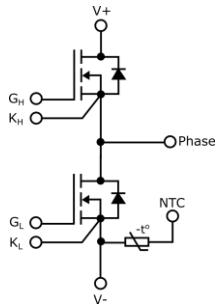
## 3300 V, 2.3 mΩ, Silicon Carbide, Half-Bridge Module

| | |
|---|---|
| $V_{DS}$ | 3300 V |
| $I_{DS}$ | 600 A |

### Technical Features

- High Power Density Footprint
- High Junction Temperature (175 °C) Operation
- Low Stray Inductance (11 nH)
- AlSiC Baseplate
- High Thermal Conductivity Silicon Nitride Substrate
- Increased Thermal-Mechanical Performance
- 3300 V Drain-Source Voltage






### Applications

- Heavy-Duty E-Mobility: Transportation and Mining
- Ultra-Fast DC Chargers
- Industrial Motor Drives
- Industrial Uninterruptable Power Supply (UPS) Systems
- Marine and Aerospace Propulsion
- Terrestrial Power Distribution Systems
- HVDC and FACTS Controllers

### System Benefits

- Reduced Volume, Weight Overall System Level Cost
- Higher Reliability
- Higher System Efficiency
- Reduced Cooling Requirements
- Improved Thermal Cycling and Longer Lifetime

### Key Parameters

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Notes |
|---|---|---|---|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | | | 3300 | V | $T_C$ = 25 °C | |
| Maximum Gate-Source Voltage | $V_{GS\,max}$ | -10 | | +25 | | Transient | Note 1 |
| Operational turn-on Gate-Source Voltage | $V_{GS\,op}$ | | +15…+18 | 20 | | Static | |
| Operational turn-off Gate-Source Voltage | $V_{GS\,op}$ | -5 | | | | | |
| DC Continuous Drain Current ($T_{VJ} \leq 175$ °C) | $I_D$ | | | 770<br>833 | A | $V_{GS}$ = 15 V, $T_C$ = 25 °C, $T_{VJ} \leq 175$ °C<br>$V_{GS}$ = 18 V, $T_C$ = 25 °C, $T_{VJ} \leq 175$ °C | Notes 2, 3, 4 |
| | | | 580<br>627 | | | $V_{GS}$ = 15 V, $T_C$ = 90 °C, $T_{VJ} \leq 175$ °C<br>$V_{GS}$ = 18 V, $T_C$ = 90 °C, $T_{VJ} \leq 175$ °C | |
| Pulsed Drain Current | $I_{DM}$ | | 1540<br>1666 | | | $t_{pmax}$ limited by $T_{VJ\,max}$<br>$V_{GS}$ = 15 V, $T_C$ = 25 °C<br>$V_{GS}$ = 18 V, $T_C$ = 25 °C | |
| Power Dissipation | $P_D$ | | 4098 | | W | $T_C$ = 25 °C, $T_{VJ} \leq 175$ °C | Note 5 |
| Operating Virtual Junction Temperature | $T_{VJ\,op}$ | -55 | | 175 | °C | | |

Note (1): Recommended turn-on gate voltage is 15 to 18 V
Note (2): Current limit $T_C$ = 25 °C imposed by package
Note (3): Current limit $T_C$ = 90 °C calculated by $I_{D(max)}=\sqrt{(P_D/R_{DS(typ)}(T_{VJ(max)}, I_{D(max)}))}$
Note (4): Verified by design
Note (5): $P_D = (T_{VJ} - T_C)/R_{TH(JC, Typ)}$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## MOSFET Characteristics (Per Position) ($T_{VJ}$ = 25 °C unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Notes |
|---|---|---|---|---|---|---|---|
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | 3300 | | | V | $V_{GS}$ = 0 V, $T_{VJ}$ = -55 °C | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 2.6 | 3.5 | 4.5 | V | $V_{DS}$ = $V_{GS}$, $I_{DS}$ = 530 mA | |
| | | | 2.6 | | | $V_{DS}$ = $V_{GS}$, $I_{DS}$ = 530 mA, $T_{VJ}$ = 175 °C | |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | | 100 | 600 | µA | $V_{GS}$ = 0 V, $V_{DS}$ = 3300 V | |
| Gate-Source Leakage Current | $I_{GSS}$ | | 200 | 5000 | nA | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | |
| Drain-Source On-State Resistance (MOSFET only) | $R_{DS(on)}$ | | 2.7<br>2.35<br>2.13 | 3.4<br>3.0<br>2.7 | mΩ | $V_{GS}$ = 15 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 25 °C<br>$V_{GS}$ = 18 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 25 °C<br>$V_{GS}$ = 20 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 25 °C | Fig. 3, 4 |
| | | | 6.8<br>5.9<br>5.4 | | | $V_{GS}$ = 15 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 175 °C<br>$V_{GS}$ = 18 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 175 °C<br>$V_{GS}$ = 20 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 175 °C | |
| Transconductance | $g_{fs}$ | | 448 | | S | $V_{DS}$ = 20 V, $I_{DS}$ = 600 A | Fig. 5 |
| | | | 536 | | | $V_{DS}$ = 20 V, $I_{DS}$ = 600 A, $T_{VJ}$ = 175 °C | |
| Turn-On Switching Energy, $T_{VJ}$ = 25 °C<br>$T_{VJ}$ = 125 °C<br>$T_{VJ}$ = 175 °C | $E_{On}$ | | 109.3<br>98.6<br>107.0 | | mJ | $V_{DD}$ = 1800 V,<br>$I_D$ = 600 A,<br>$V_{GS}$ = -5 V/18 V,<br>$R_{G-ON(ext)}$ = 1.5 Ω, $R_{G-OFF(ext)}$ = 1.5 Ω,<br>$L_\sigma$ = 7 nH | Fig 25 |
| Turn-Off Switching Energy, $T_{VJ}$ = 25 °C<br>$T_{VJ}$ = 125 °C<br>$T_{VJ}$ = 175 °C | $E_{Off}$ | | 50.0<br>46.3<br>48.7 | | | | |
| Internal Gate Resistance | $R_{G(int)}$ | | 0.5 | | Ω | f = 100 kHz, $V_{AC}$ = 25 mV | |
| Input Capacitance | $C_{iss}$ | | 146 | | nF | $V_{GS}$ = 0 V, $V_{DS}$ = 3000 V,<br>$V_{AC}$ = 25 mV, f = 100 kHz | Fig. 11 |
| Output Capacitance | $C_{oss}$ | | 1.8 | | | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | 53 | | pF | | |
| Gate to Source Charge | $Q_{GS}$ | | 1327 | | nC | $V_{DS}$ = 1800 V, $V_{GS}$ = -5 V/+18 V<br>$I_D$ = 600 A<br>Per IEC60747-8-4 pg 21 | Fig. 19 |
| Gate to Drain Charge | $Q_{GD}$ | | 803 | | | | |
| Total Gate Charge | $Q_G$ | | 3492 | | | | |
| FET Thermal Resistance, Junction to Case | $R_{th\ JC}$ | | 0.037 | | °C/W | | Fig. 33 |

## Diode Characteristics (Per Position) ($T_{VJ}$ = 25 °C unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions | Notes |
|---|---|---|---|---|---|---|---|
| Body Diode Forward Voltage | $V_{SD}$ | | 6.0 | | V | $V_{GS}$ = -5 V, $I_{SD}$ = 600 A | Fig. 9 |
| | | | 5.3 | | V | $V_{GS}$ = -5 V, $I_{SD}$ = 600 A, $T_{VJ}$ = 175 °C | |
| Reverse Recovery Time | $t_{RR}$ | | 140 | | ns | $V_{GS}$ = -5 V, $I_{SD}$ = 600 A, $V_R$ = 1800 V;<br>$di_f/dt$ = 6.5 A/ns, $R_{G(ON)}$ = 1.5 Ω,<br>$T_{VJ}$ = 175 °C, | |
| Reverse Recovery Charge | $Q_{RR}$ | | 23.9 | | µC | | |
| Peak Reverse Recovery Current | $I_{RRM}$ | | 267 | | A | | |
| Reverse Recovery Energy,<br>$T_{VJ}$ = 25 °C<br>$T_{VJ}$ = 125 °C<br>$T_{VJ}$ = 175 °C | $E_{RR}$ | | 1.73<br>2.34<br>23.7 | | mJ | $V_{DD}$ = 1800 V, $I_D$ = 600 A,<br>$V_{GS}$ = -5 V/18 V, $R_{G-ON(ext)}$ = 1.5 Ω,<br>$L_\sigma$ = 7 nH | Fig. 27 |

## Temperature Sensor (NTC) Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| Resistance at 25 °C | $R_{25}$ | | 4700 | | Ω | $T_{NTC}$ = 25 °C |
| Tolerance of $R_{25}$ | | | | ±1 | % | |
| Beta Value for 25 °C to 85 °C | $B_{25/85}$ | | 3435 | | K | |
| Beta Value for 0 °C to 100 °C | $B_{0/100}$ | | 3399 | | K | |
| Tolerance of $B_{25/85}$ | | | | ±1 | % | |
| Maximum Power Dissipation | $P_{25}$ | | | 50 | mW | |

## Steinhart & Hart Coefficients for NTC Resistance & NTC Characteristics Computation (T in K)

$$\ln\left(\frac{R}{R_{25}}\right) = A + \frac{B}{T} + \frac{C}{T^2} + \frac{D}{T^3}$$

| A | B | C | D |
|---|---|---|---|
| -1.289E+01 | 4.245E+03 | -8.749E+04 | -9.588E+06 |

$$\frac{1}{T} = A_1 + B_1 \ln\left(\frac{R}{R_{25}}\right) + C_1 \ln^2\left(\frac{R}{R_{25}}\right) + D_1 \ln^3\left(\frac{R}{R_{25}}\right)$$

| $A_1$ | $B_1$ | $C_1$ | $D_1$ |
|---|---|---|---|
| 3.354E-03 | 3.001E-04 | 5.085E-06 | 2.188E-07 |

## Module Physical Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| Package Resistance, M1 (High-Side) | $R_{1-3}$ | | 0.28 | | mΩ | $T_C$ = 125 °C, Note 6 & 7 |
| Package Resistance, M2 (Low-Side) | $R_{3-6}$ | | 0.55 | | mΩ | $T_C$ = 125 °C, Note 6 & 7 |
| Stray Inductance | $L_{Stray}$ | | 11 | | nH | Between Terminals 1 & 6, f = 10 MHz |
| Case Temperature | $T_C$ | -55 | | 150 | °C | |
| Storage Temperature | $T_{stg}$ | -55 | | 150 | °C | |
| Mounting Torque | M | 3.5 | 4.5 | 5.5 | N-m | Baseplate, M6 bolts |
| | | 8 | 12 | 16 | | Power Terminals, M8 bolts |
| | | 0.5 | 0.7 | 1.3 | | Auxiliary Terminals, M3 bolts |
| Weight | W | | 745 | | g | |
| Case Isolation Voltage | | 6.0 | | | kV | AC, 50 Hz, 1 minute |
| Comparative Tracking Index | CTI | 600 | | | | |
| Clearance Distance | | 11 | | | mm | Terminal to Terminal |
| | | 33 | | | | Terminal to Baseplate |
| Creepage Distance | | 23 | | | | Terminal to Terminal |
| | | 45 | | | | Terminal to Baseplate |

Note (6): Total Effective Resistance (Per Switch Position) = MOSFET $R_{DS(ON)}$ + Switch Position Package Resistance
Note (7): Numbers reference the connections from the Schematics and Pin Out section of this document

## Typical Performance

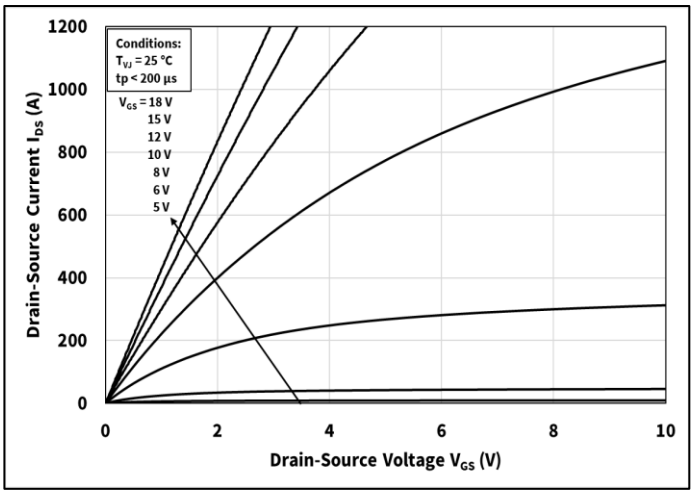



**Figure 1.** Output Characteristics for Various Gate Voltages at a junction temperature of 25 °C

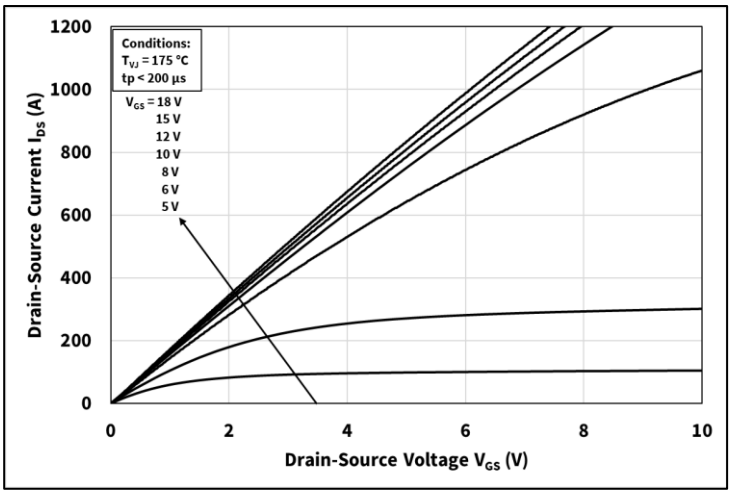



**Figure 2.** Normalized On-State Resistance vs. Drain Current at a junction temperature of 175 °C

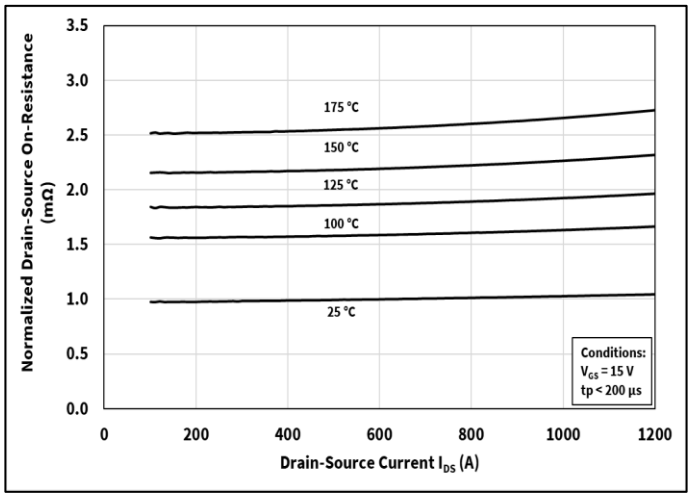



**Figure 3.** Normalized On-State Resistance vs. Drain Current ($V_{GS}$ = 15 V)

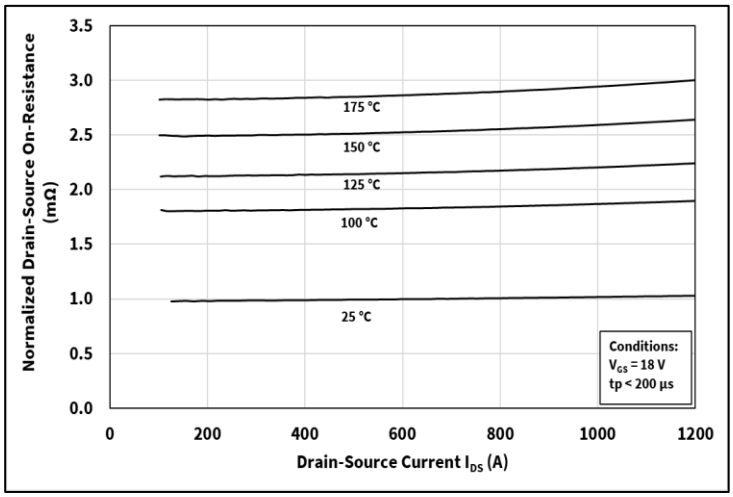



**Figure 4.** Normalized On-State Resistance vs Drain Current ($V_{GS}$ = 18 V)

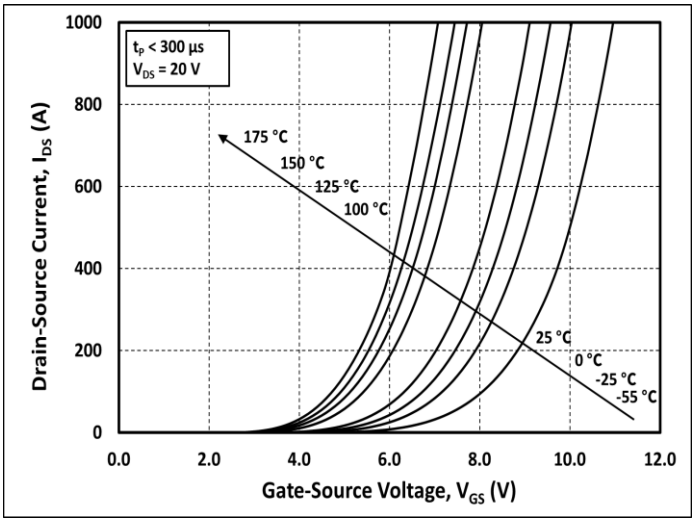



**Figure 5.** Transfer Characteristics for Various Junction Temperatures

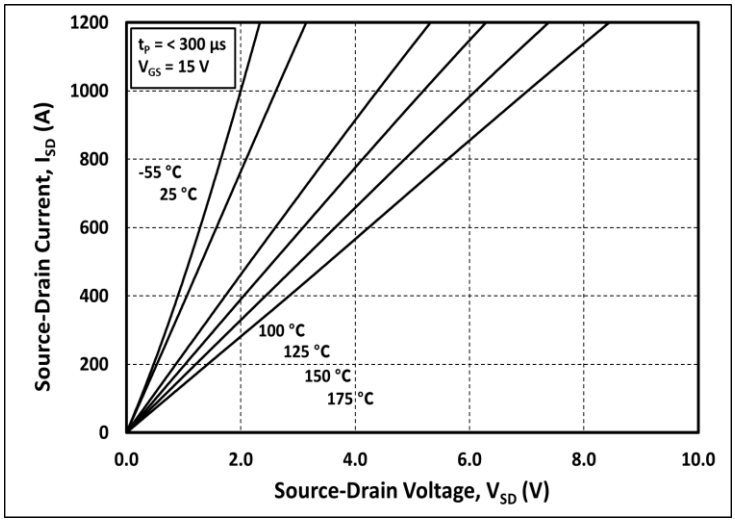



**Figure 6.** 3rd Quadrant Characteristic vs. Junction Temperatures at $V_{GS}$ = 15 V

## Typical Performance

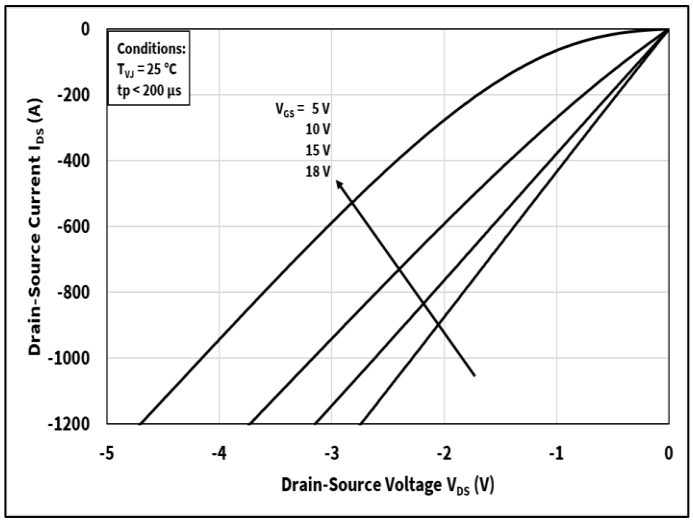



**Figure 7.** 3rd Quadrant Characteristic for Various Gate Bias voltages at a junction temperature of 25 °C

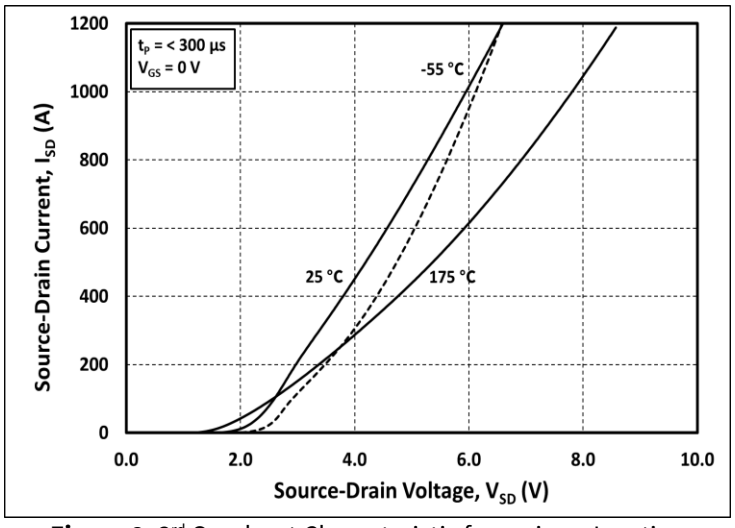



**Figure 8.** 3rd Quadrant Characteristic for various Junction Temperatures at $V_{GS}$ = 0 V

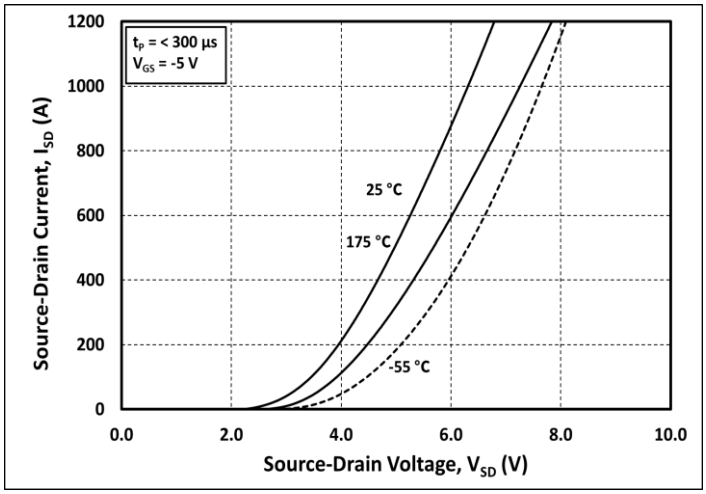



**Figure 9.** 3rd Quadrant Characteristics vs. Junction Temperatures at $V_{GS}$ = -5 V (Body Diode)

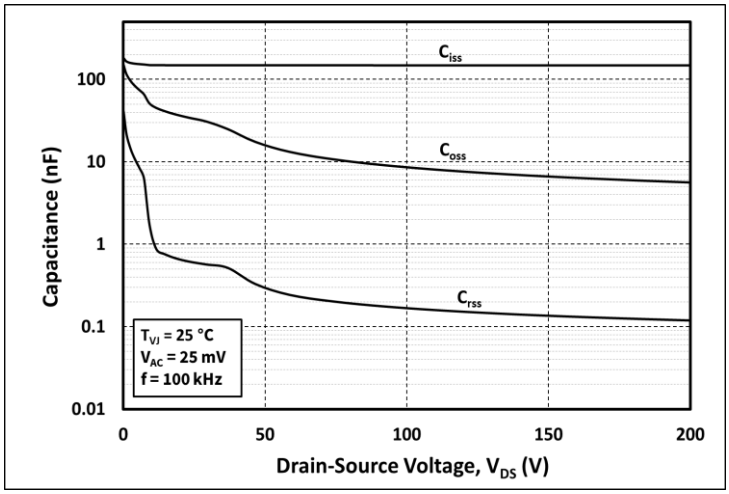



**Figure 10.** Typical Capacitances vs. Drain to Source Voltage (0 – 200 V)

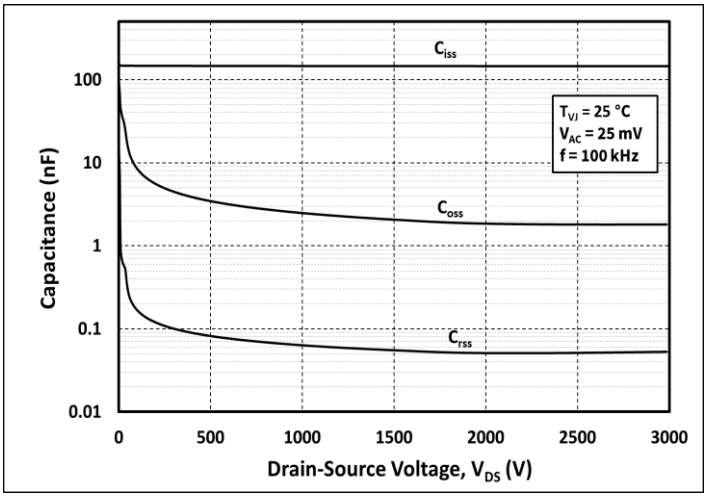



**Figure 11.** Typical Capacitances vs. Drain to Source Voltage (0 – 3000 V)

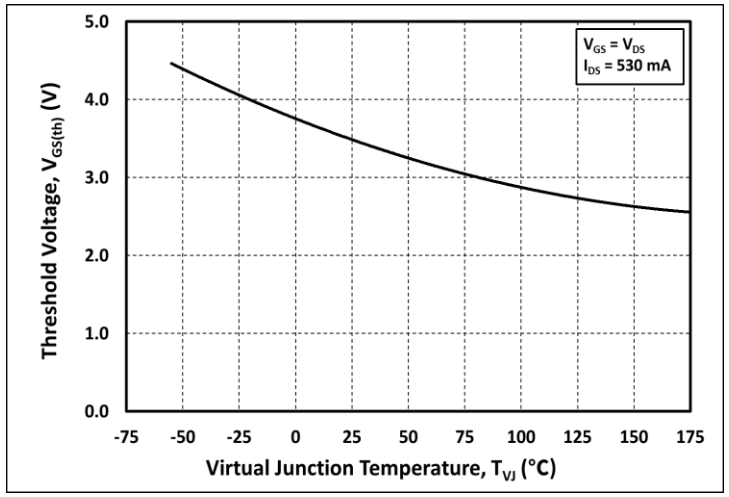



**Figure 12.** Threshold Voltage vs. Junction Temperature

## Typical Performance

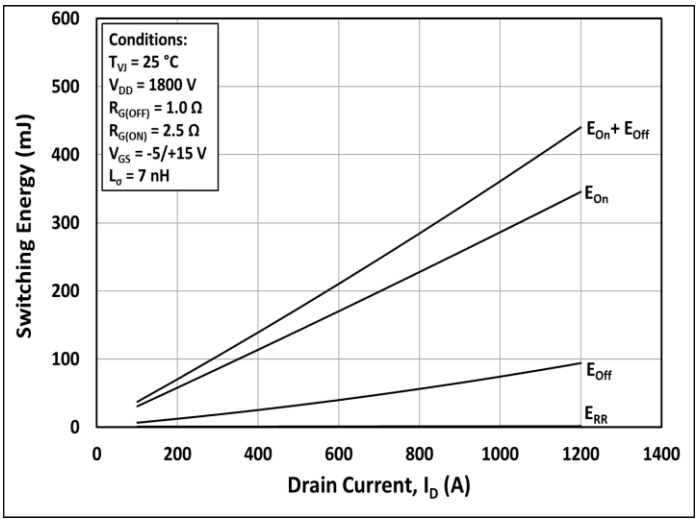



**Figure 13.** Switching Energy vs Drain Current ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+15 V)

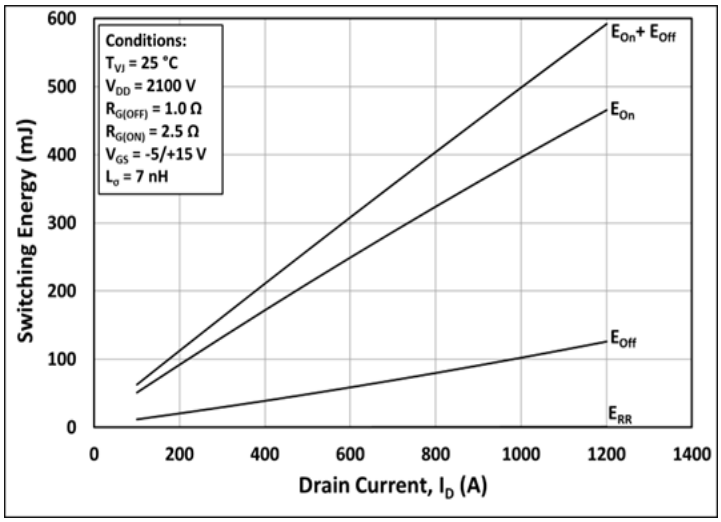



**Figure 14.** MOSFET Switching Energy vs. Drain Current ($V_{DD}$ = 2100 V, $V_{GS}$ = -5/+15 V)

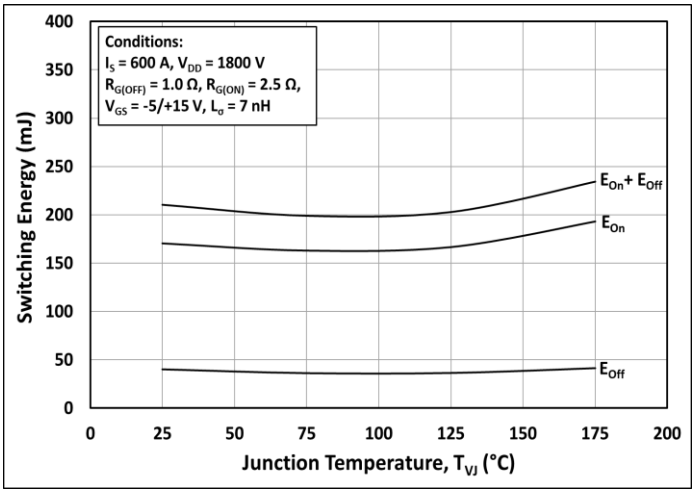



**Figure 15.** MOSFET Switching Energy vs. Junction Temperature ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+15 V)

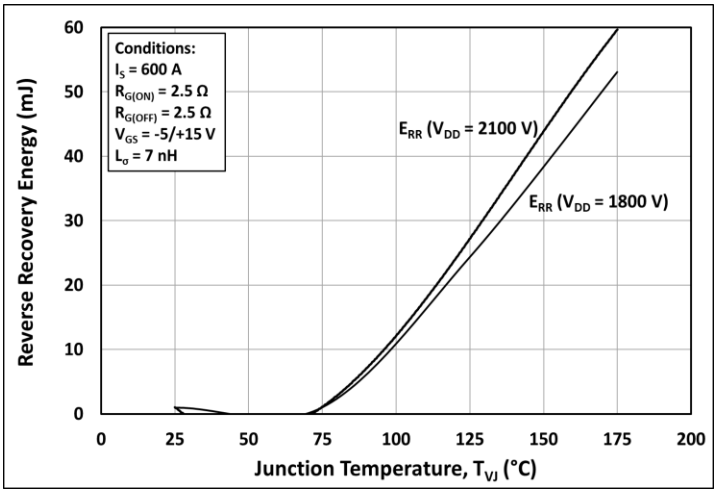



**Figure 16.** Reverse Recovery Energy vs. Junction Temperature ($V_{GS}$ = -5/+15 V)

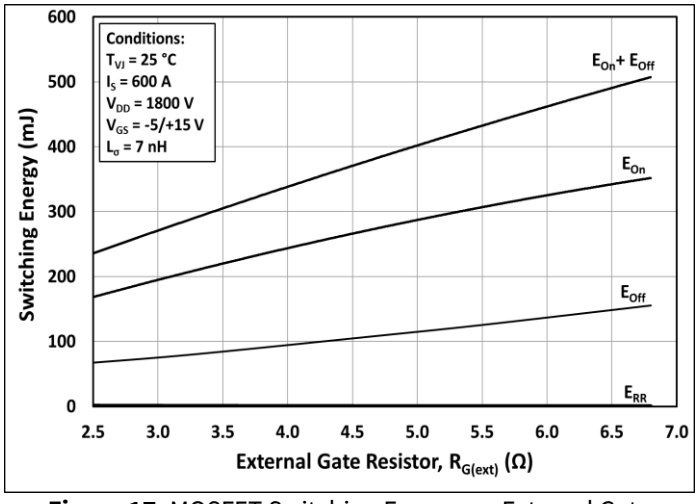



**Figure 17.** MOSFET Switching Energy vs. External Gate Resistance ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+15 V)

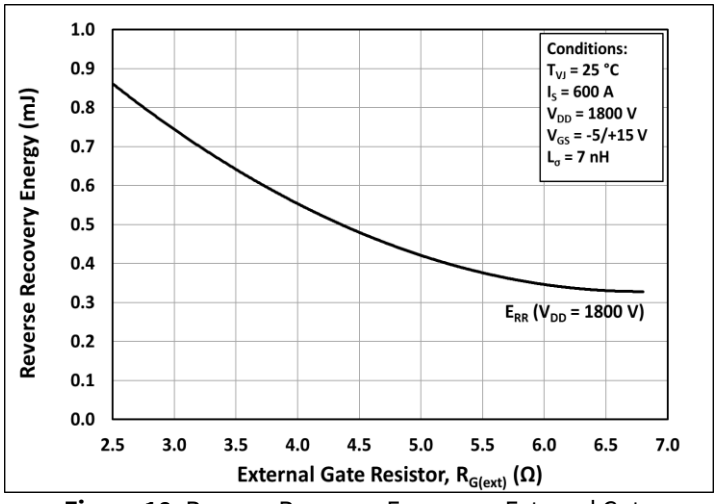



**Figure 18.** Reverse Recovery Energy vs. External Gate Resistance ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+15 V)

## Typical Performance

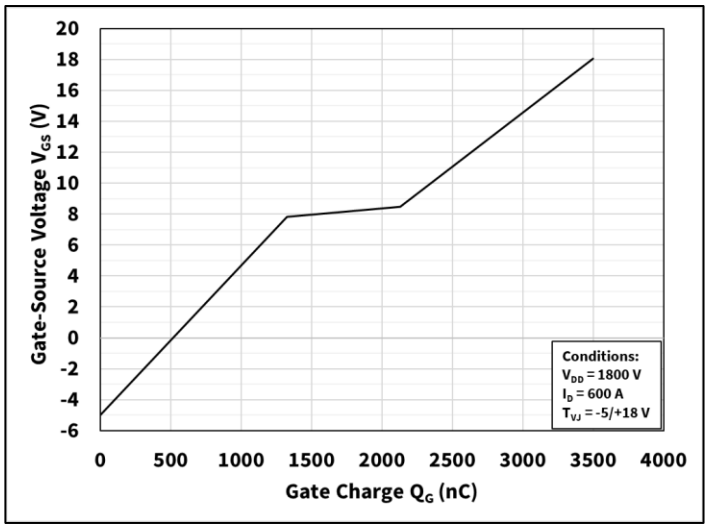



**Figure 19.** Gate Charge Characteristics

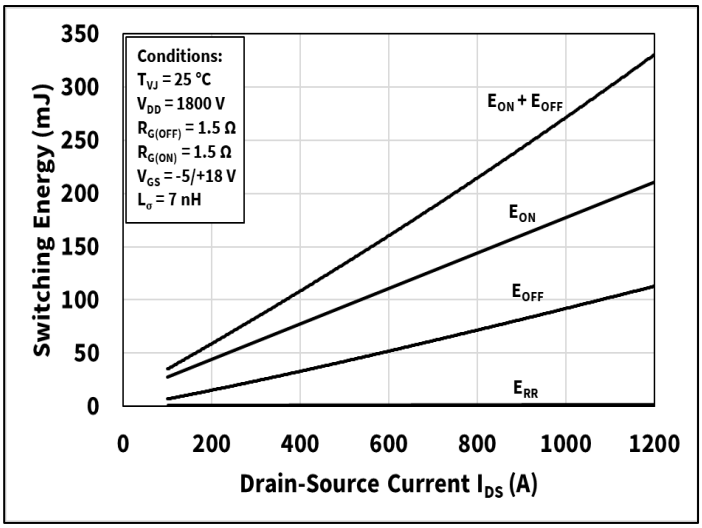



**Figure 20.** Switching Energy vs. Drain Current ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+18 V, $T_{VJ}$ = 25 °C)

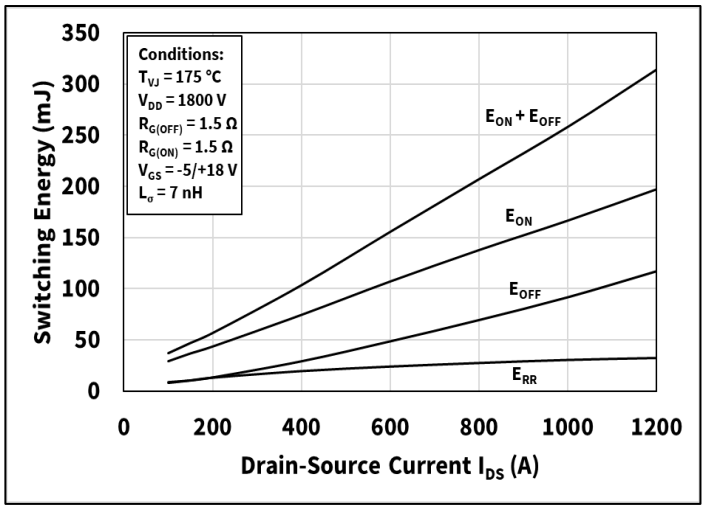



**Figure 21.** Switching Energy vs Drain Current ($V_{DD}$ = 1800 V, $V_{GS}$ = -5/+18 V, $T_{VJ}$ = 175 °C)

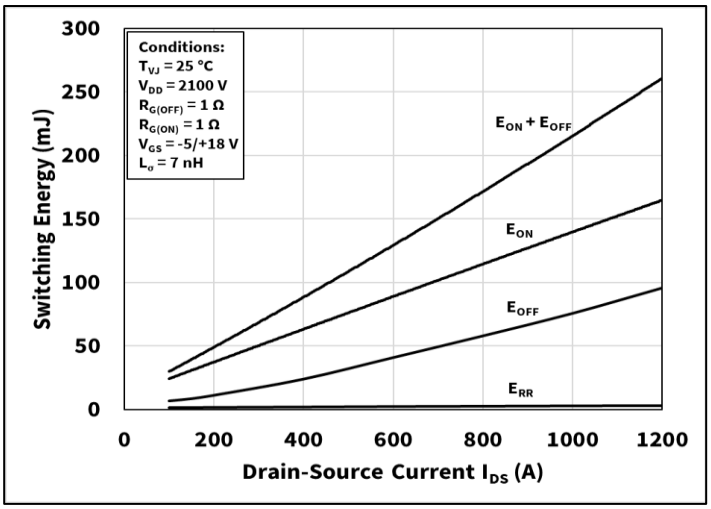



**Figure 22.** Switching Energy vs Drain Current ($V_{DD}$ = 2100 V, $V_{GS}$ = -5/+18 V, $T_{VJ}$ = 25 °C)

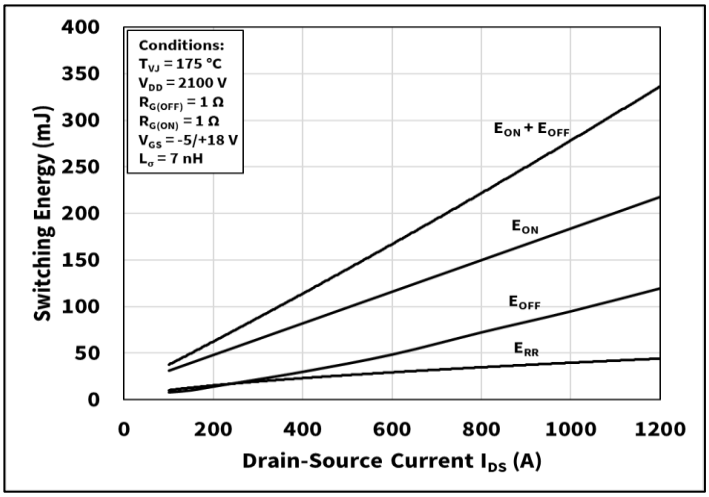



**Figure 23.** Switching Energy vs Drain Current ($V_{DD}$ = 2100 V, $V_{GS}$ = -5/+18 V, $T_{VJ}$ = 175 °C)

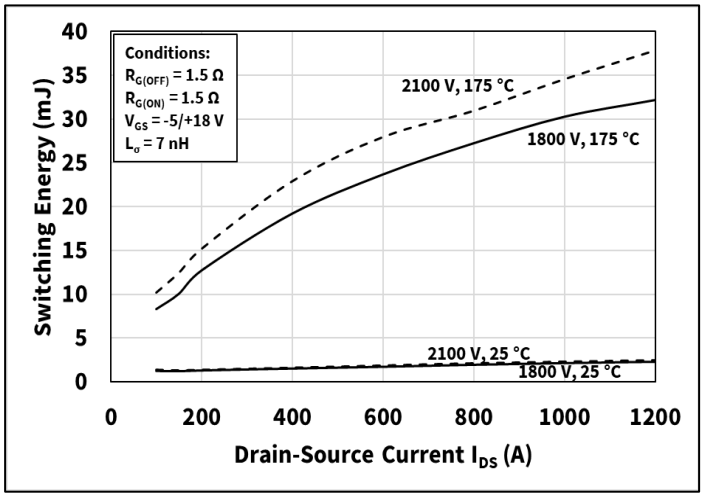



**Figure 24.** Reverse Recovery vs. Drain Current ($V_{GS}$ = 18 V)

## Typical Performance

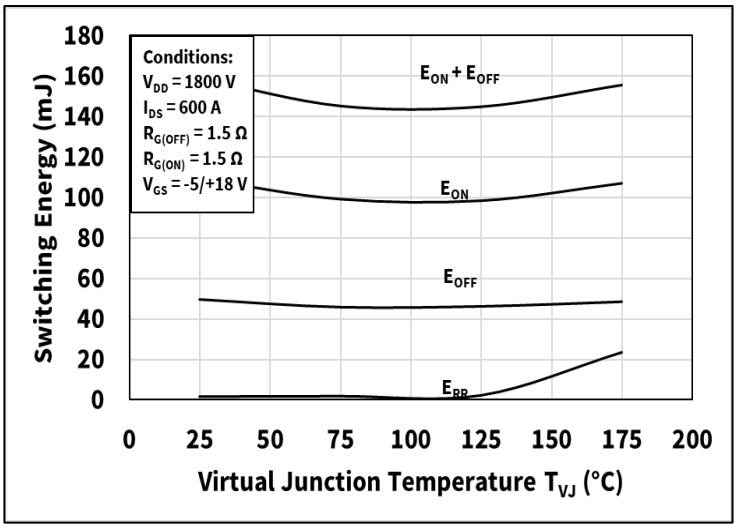



**Figure 25.** Switching Energy vs. Junction Temperature (1800 V, 600 A, $V_{GS}$ = -5/+18 V)

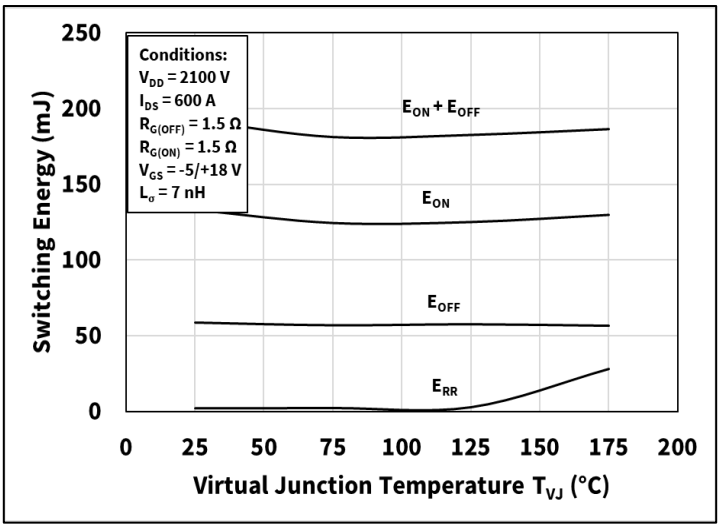



**Figure 26.** Switching Energy vs. Junction Temperature (2100 V, 600 A)

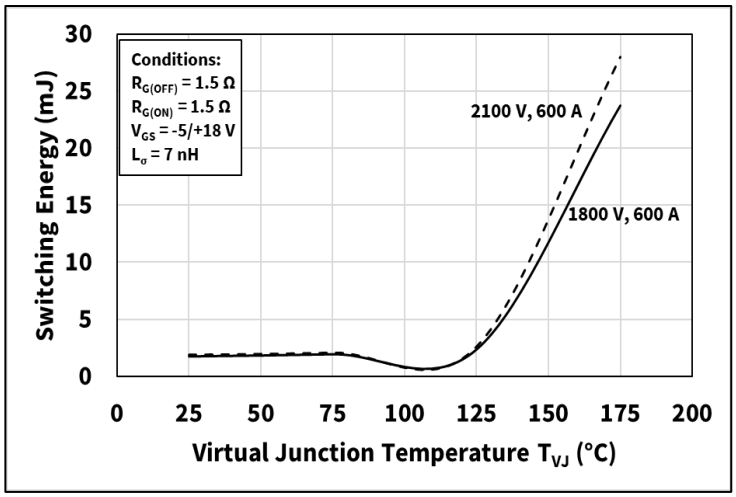



**Figure 27.** Reverse Recovery Switching Loss vs. Junction Temperature ($V_{GS}$ = -5/+18 V)

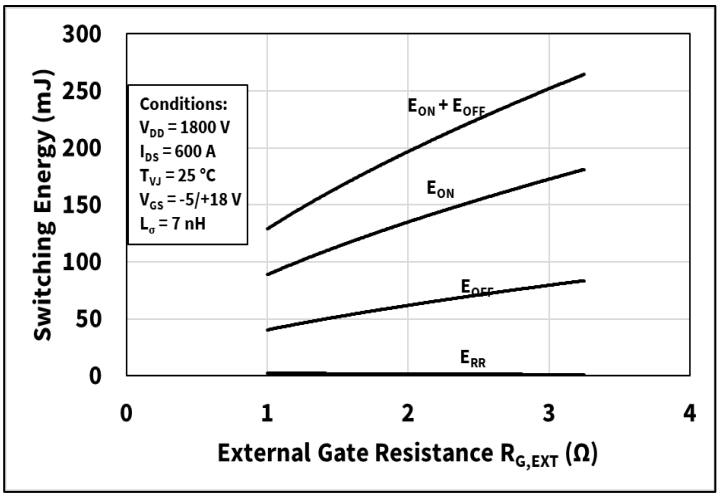



**Figure 28.** Switching Energy vs External Gate Resistance (1800 V, 600 A, 25 °C)

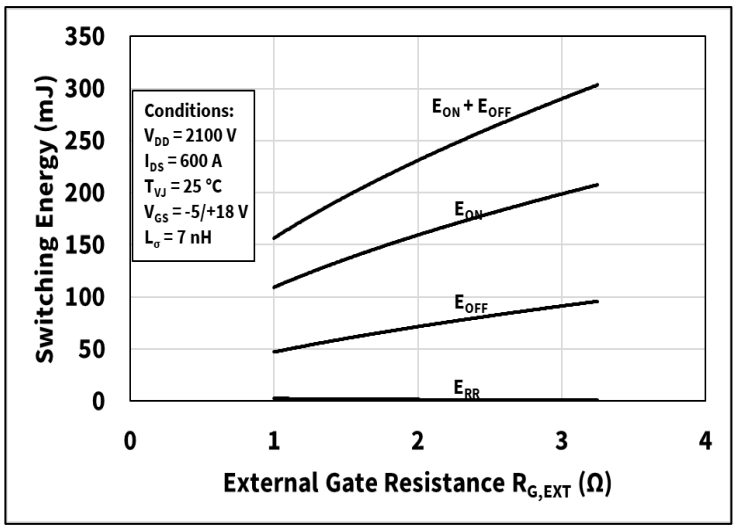



**Figure 29.** Switching Energy vs.External Gate Resistance (2100 V, 600 A, 25 °C)

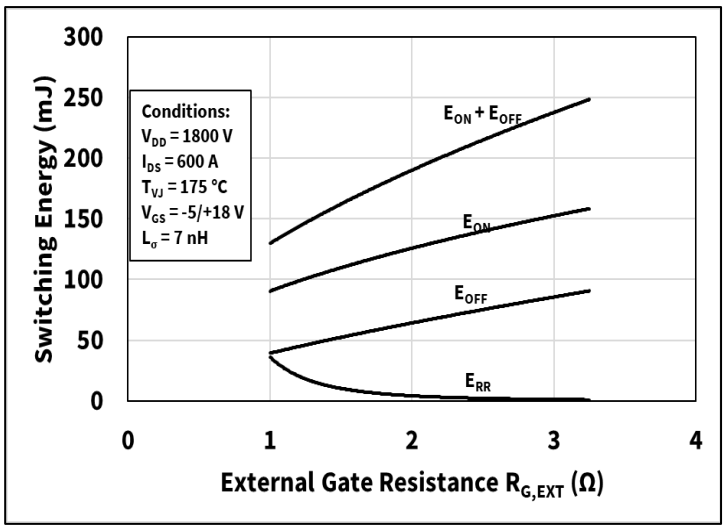



**Figure 30.** Switching Energy vs.External Gate Resistance (1800 V, 600 A, 175 °C)

## Typical Performance

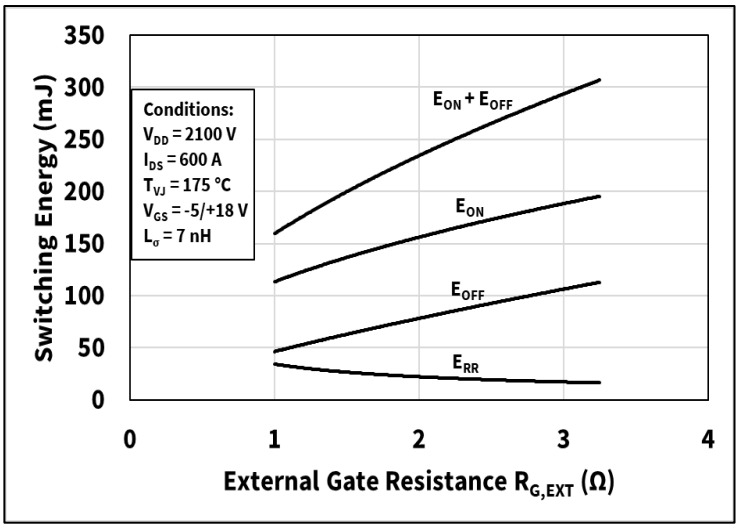



**Figure 31.** Switching Energy vs.External Gate Resistance (2100 V, 600 A, -5/+18V, 175 °C)

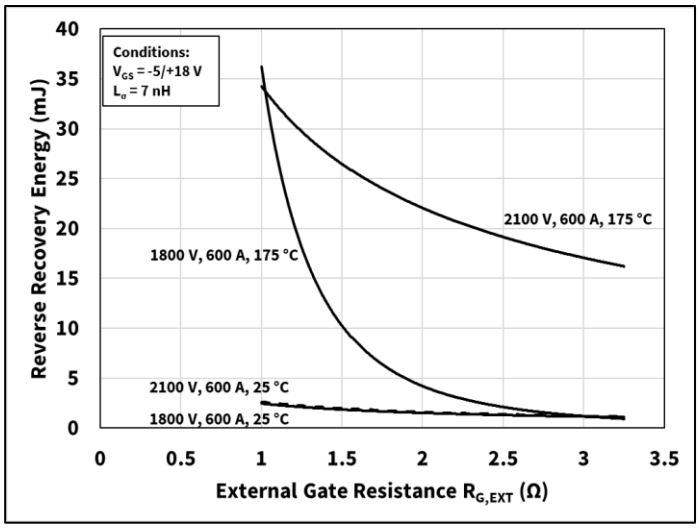



**Figure 32.** Reverse Recovery Energy vs External Gate Resistance ($V_{GS}$ = -5/+18 V, 1200 A)

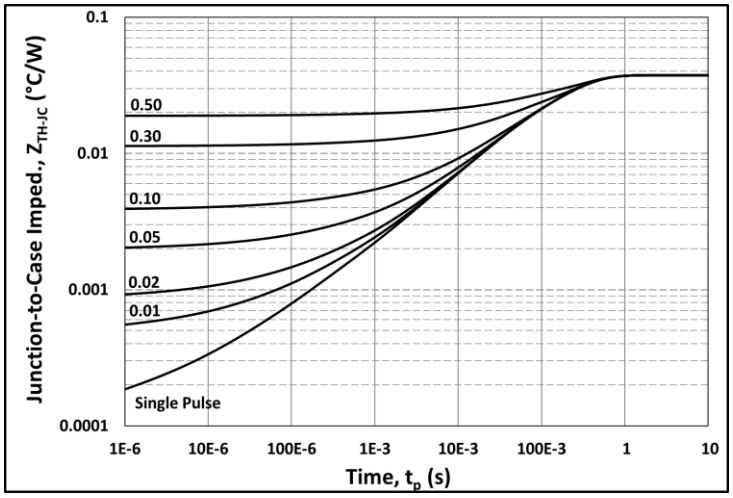



**Figure 33.** MOSFET Junction to Case Transient Thermal Impedance, $Z_{TH,JC}$ (°C/W)

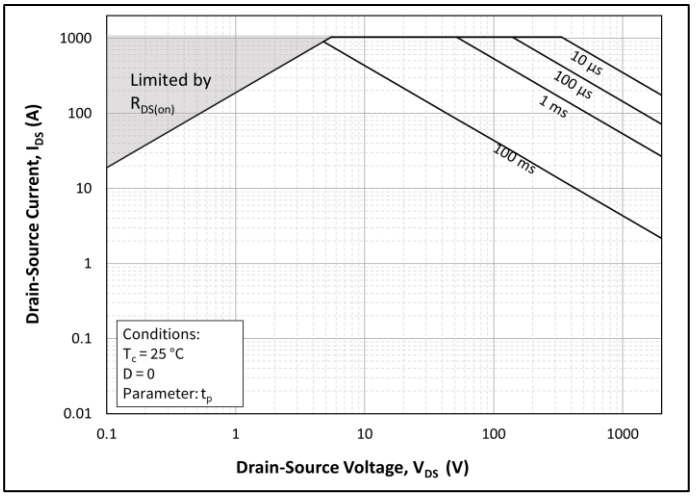



**Figure 34.** Forward Bias Safe Operating Area (FBSOA)

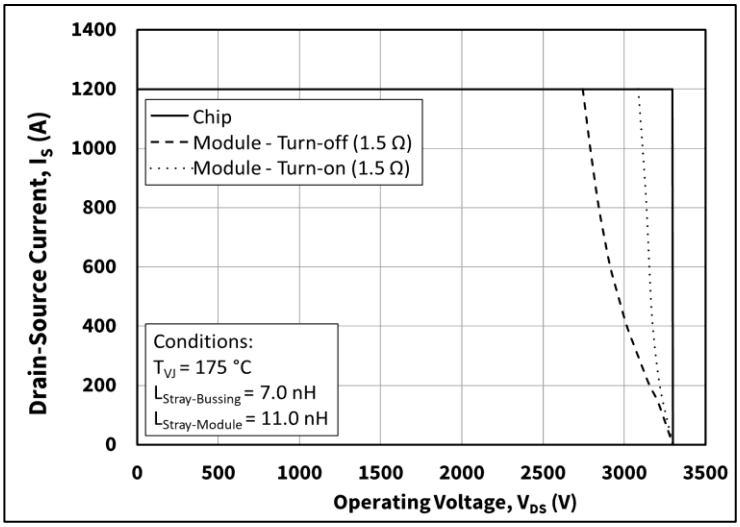



**Figure 35.** Reverse Bias Safe Operating Area (RBSOA)

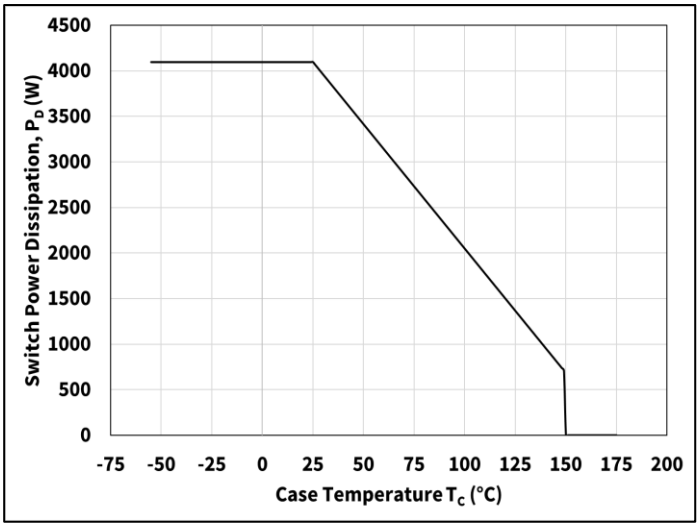



**Figure 36.** Maximum Power Dissipation vs. Case Temperature

## Typical Performance

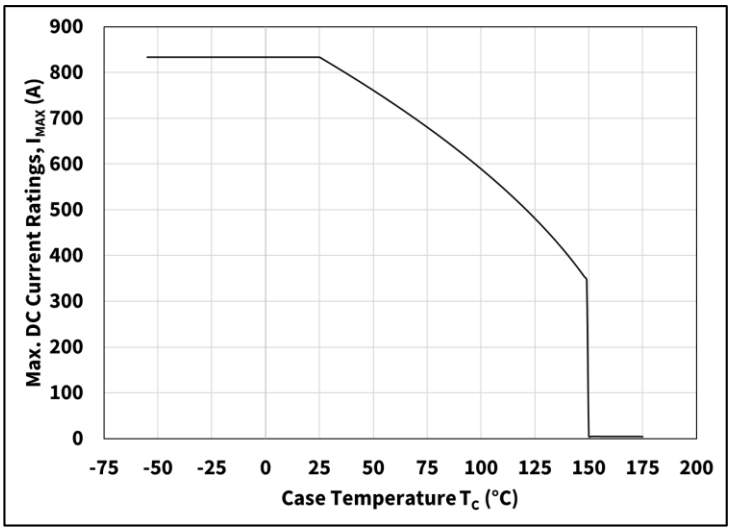



**Figure 37.** Continuous Drain Current Derating vs. Case Temperature

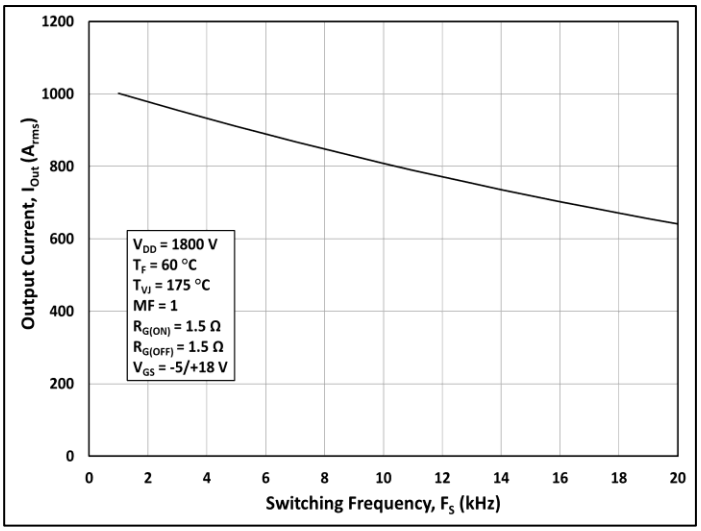



**Figure 38.** Typical Output Current Capability vs. Switching Frequency (Inverter Application)

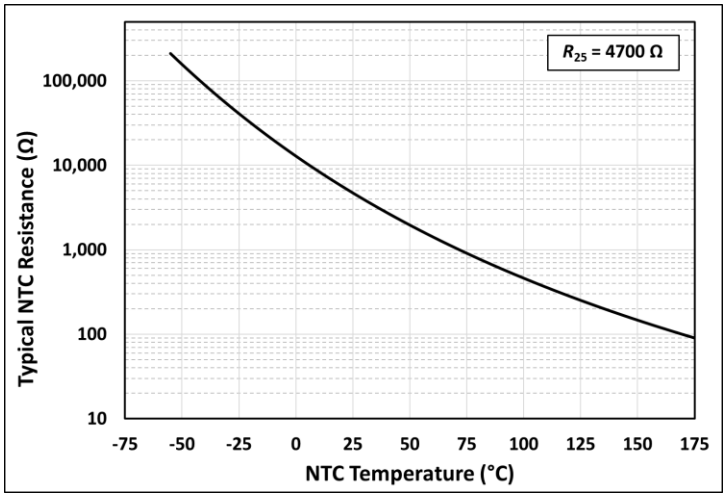



**Figure 39.** NTC Resistance vs NTC Temperature

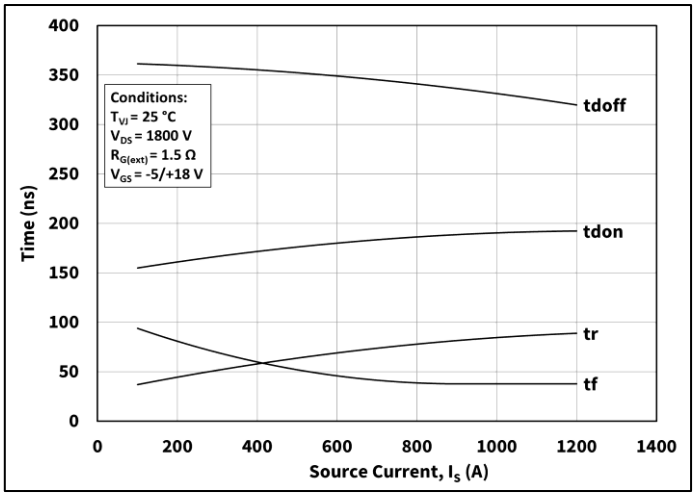



**Figure 40.** Timing vs Source Current

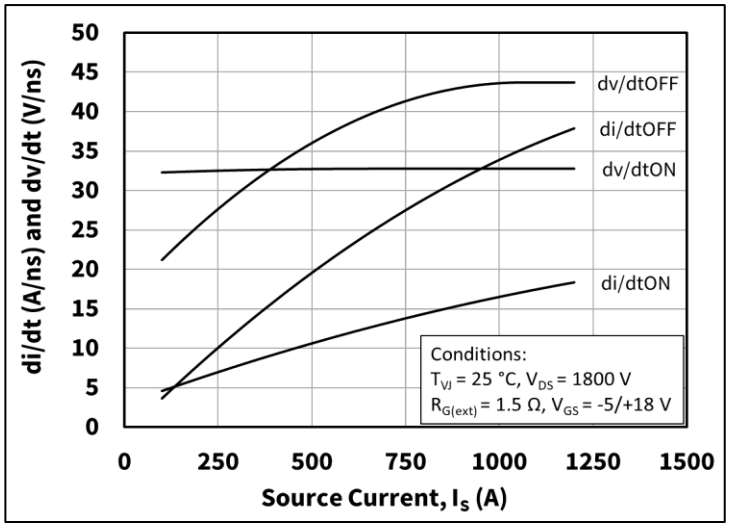



**Figure 41.** dv/dt and di/dt vs. Source Current

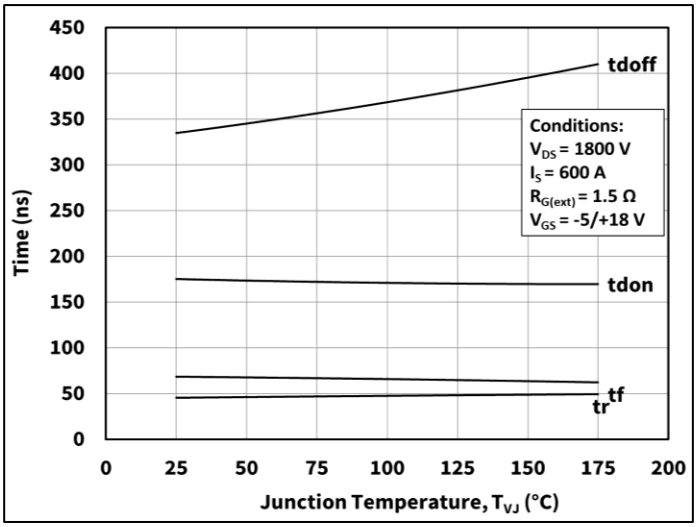



**Figure 42.** Timing vs Junction Temperature

## Typical Performance

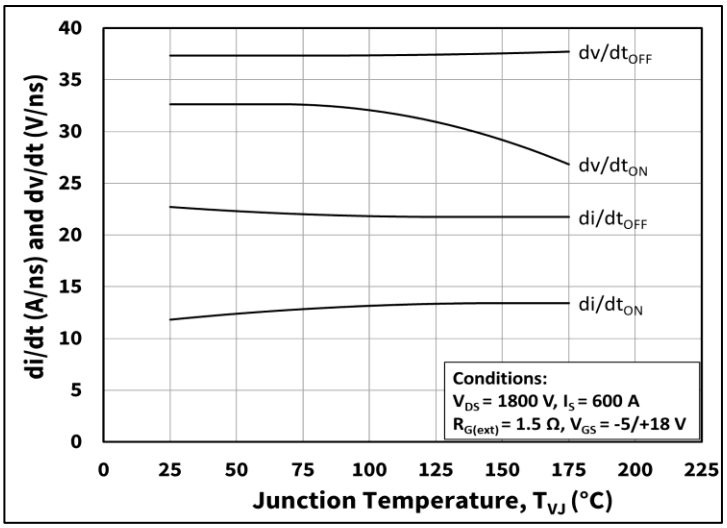



**Figure 43.** dv/dt and di/dt vs. Junction Temperature

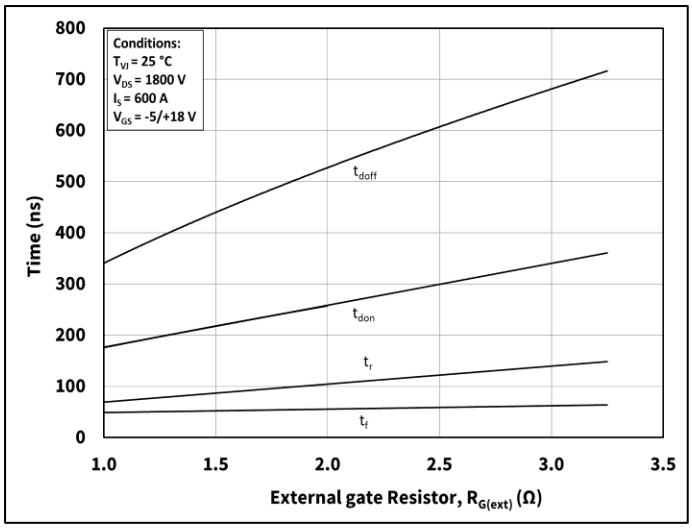



**Figure 44.** Timing vs External Gate Resistance

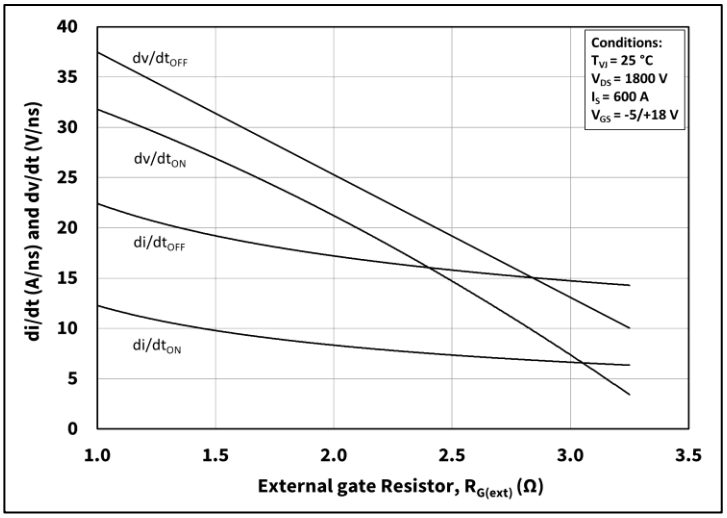



**Figure 45.** dv/dt and di/dt vs. External Gate Resistance

## Definitions

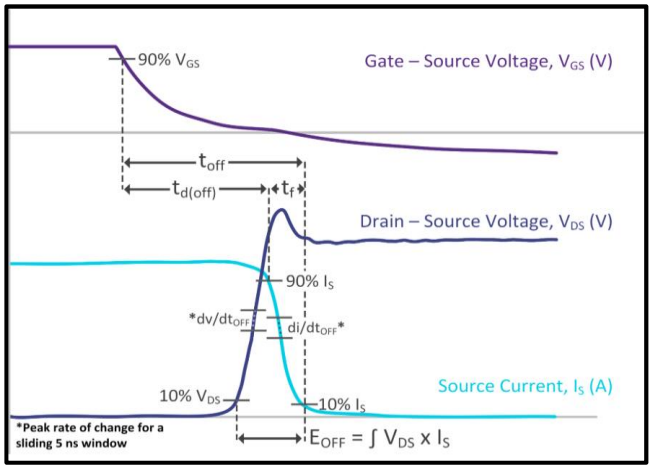



**Figure 46.** Turn-off Transient Definitions

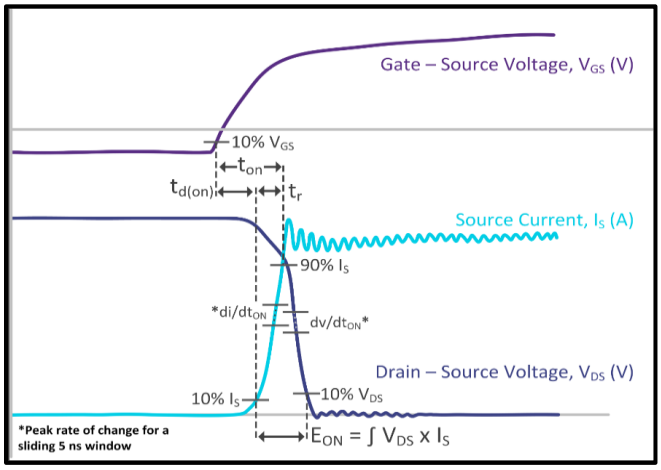



**Figure 47.** Turn-on Transient Definitions

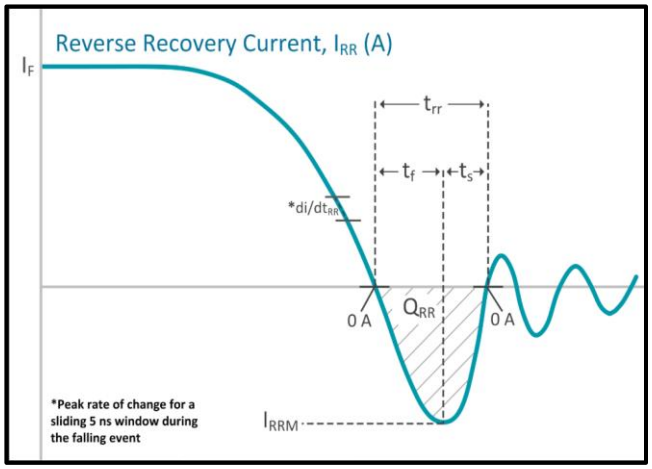



**Figure 48.** Reverse Recovery Definitions

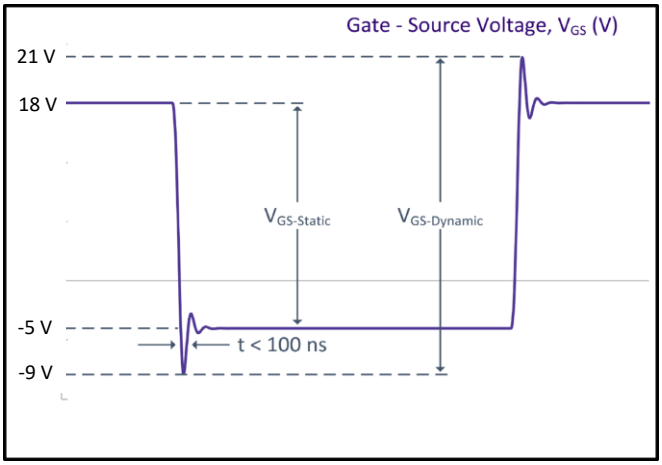
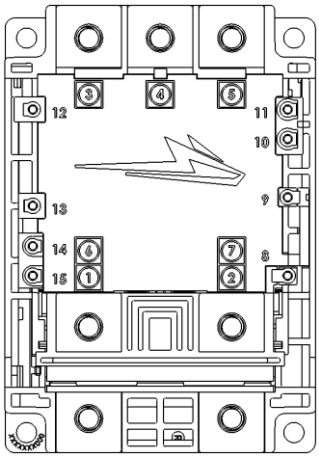
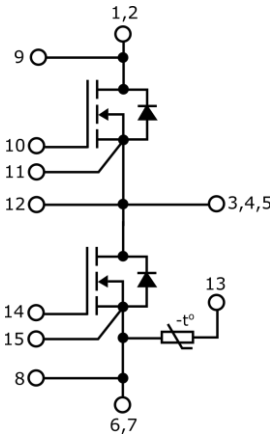
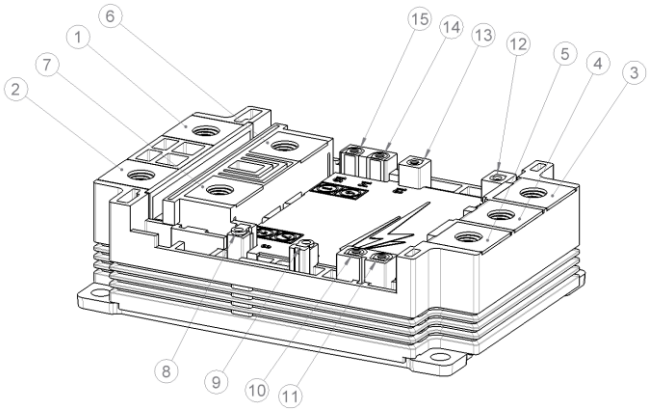



**Figure 49.** $V_{GS}$ Transient Defintions

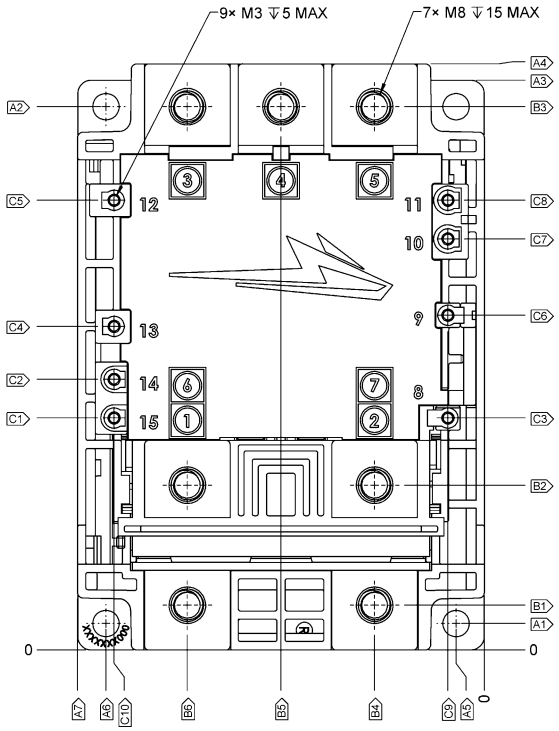
## Schematic and Pinout

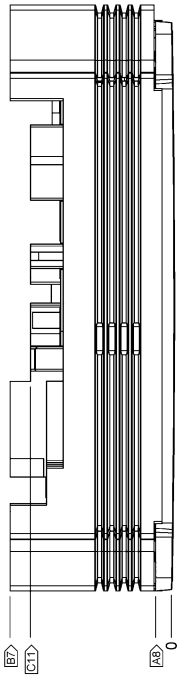





## Package Dimensions (mm)




| DIMENSION TABLE | | |
|---|---|---|
| SYMBOL | DIMENSION | TOLERANCE |
| A1 | 2× 6.5 | ±1.0 |
| A2 | 2× 133.5 | ±1.0 |
| A3 | 140 | ±0.75 |
| A4 | 144 | ±0.5 |
| A5 | 2× 7 | ±0.75 |
| A6 | 2× 93 | ±0.75 |
| A7 | 99.9 | ±0.5 |
| A8 | 3.9 | ±0.3 |
| B1 | 2× 11 | ±0.5 |
| B2 | 2× 40.5 | ±0.5 |
| B3 | 3× 133.5 | ±0.5 |
| B4 | 3× 27 | ±0.5 |
| B5 | 50 | ±0.5 |
| B6 | 3× 73 | ±0.5 |
| B7 | 39.6 | ±0.75 |
| C1 | 57 | ±0.4 |
| C2 | 66.5 | ±0.4 |
| C3 | 57 | ±0.6 |
| C4 | 79.5 | ±0.4 |
| C5 | 110.5 | ±0.4 |
| C6 | 82.3 | ±0.5 |
| C7 | 101 | ±0.4 |
| C8 | 110.5 | ±0.4 |
| C9 | 4× 9 | ±0.6 |
| C10 | 4× 91 | ±0.6 |
| C11 | 34.6 | ±0.75 |

## Supporting Links & Tools

**Evaluation Tools & Support**

- LTspice and PLECS Models
- KIT-CRD-CIL33N-LM: Dynamic Performance Evaluation for the LM3 Module
- SpeedFit 2.0 Design Simulator™
- Technical Support Forum

**Dual-Channel Gate Driver Board**

- CGD3300HB6P-LM3: Dual Channel Differential Isolated Half-Bridge Gate Driver Board

**Application Notes**

- LM Module Signal Pinout Clarification Guide
- LM Module Platform Mounting Guide
- LM3 Thermal Interface Material Application User Guide

## Revision History

| Revision | Date | Description of Changes |
|---|---|---|
| **1** | 04/28/2023 | Initial Release |
| **2** | 09/20/2024 | Disclaimers Update |
| **3** | 08/15/2026 | Updated Mounting Torque guidance |
| **4** | 03/02/2026 | Added upgraded dynamic performance results for faster switching with 18 V and 1.5 Ω external Rg |

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